

**CLAIMS**

1. A variable capacitance formed in a semiconductor substrate with a ribbed surface, having a first electrode formed of all the ribs protruding from the substrate, of portions of the substrate underlying the ribs, and of at least portions of the substrate  
5 separating the bases of two ribs, and having a second electrode superposed to at least one portion of the first electrode, wherein the ribs are irregular in terms of planar base surface area.
2. The capacitance of claim 1, wherein two successive ribs exhibit non-  
10 parallelepiped shaped trapezoidal bases of same surface areas.
3. The capacitance of claim 2, wherein two successive ribs are arranged in quincunx.
- 15 4. The capacitance of claim 1, wherein two successive ribs exhibit non-rectangulared shaped trapezoidal bases of different surface areas.